This product complies with the RoHS Directive (EU 2002/95/EC).

2PG009

Silicon N-channel enhancement IGBT

For plasma display panel drive For high speed switching circuits

■ Features

- \bullet Low collector-emitter saturation voltage: $V_{\text{CE(sat)}}\!<\!2.5~\text{V}$
- High-speed switching: $t_f = 185 \text{ ns (typ.)}$

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-emitter voltage (E-B short)	V _{CES}	510	V	
Gate-emitter voltage (E-B short)	V _{GES}	-30 to +35	V	
Collector current	I_{C}	40	A	
Peak collector current *	I _{CP}	230	A	
Danier dissination	D	40	W	
Power dissipation $T_a = 25^{\circ}C$	P_{C}	2.0	W	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Note) *: Assurance of repetitive pulse. (Repetitive period $\leq 5 \mu s$ on-duty $\leq 20\%$)

But, it must stay within 40% of all that the time impressed pulse repetitively.



Thermal resistance (ch-a)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (E-B short)	V _{CES}	$I_C = 1 \text{ mA}, V_{GE} = 0$	510	9.		V
Collector-emitter cutoff current (E-B short) *	I _{CES}	$V_{CE} = 408 \text{ V}, V_{GE} = 0$	2000		5.0	μΑ
Gate-emitter cutoff current (E-B short)	I_{GES}	$V_{GE} = \pm 35 \text{ V}, -30 \text{ V}, V_{CE} = 0$	19		±1.0	μΑ
Gate-emitter threshold voltage	V _{GE(th)}	$V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ mA}$	3.0		5.5	V
Collector-emitter saturation voltage	V _{CE(sat)}	$V_{GE} = 15 \text{ V}, I_{C} = 40 \text{ A}$		1.95	2.5	V
Collector-emitter reverse break down voltage	-V _{CE}	$I_C = -100 \text{ mA}, V_{GE} = 15 \text{ V}$	18	22.5		V
Short-circuit input capacitance (Common emitter)	Cies	isli wh		1210		pF
Short-circuit output capacitance (Common emitter)	C _{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$		125		pF
Reverse transfer capacitance (Common emitter)	C _{res}	Cos Ville		21		pF
Gate charge load	Qg			51		nC
Gate-emitter charge	Q_{ge}	$V_{CC} = 250 \text{ V}, I_C = 40 \text{ A}, V_{GE} = 15 \text{ V}$		9		nC
Gate-collector charge	Q_{gc}			20		nC
Turn-on delay time	t _{d(on)}			75		ns
Rise time	t _r	$V_{CC} = 250 \text{ V}, I_C = 40 \text{ A},$		610		ns
Turn-off delay time	$t_{d(off)}$	$RL \approx 6.25 \Omega$, $V_{GE} = 15 V$		200		ns
Fall time	t_{f}			185	300	ns
Thermal resistance (ch-c)	R _{th(ch-c)}				3.13	°C/W

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

 $R_{th(j-a)}$

Package

Code

TO-220D-A1

- Marking Symbol: 2PG009
- Pin Name
 - 1. Gate
 - 2. Collector
 - 3. Emitter

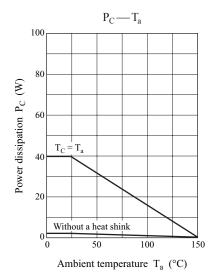
Internal Connection

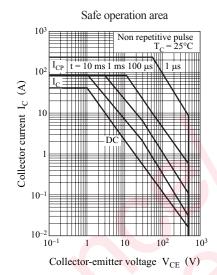


63

°C/W

2PG009 Panasonic

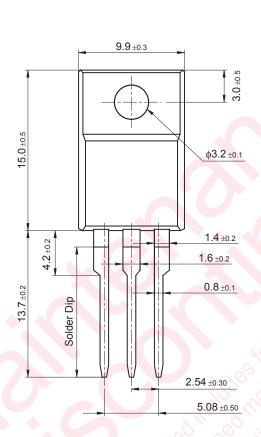


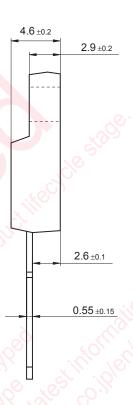


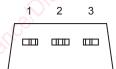
2 SJN00007AED

TO-220D-A1

Unit: mm







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